

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

5 Claim 1 (previously presented) A method of double-sided etching, comprising:
 providing a wafer comprising at least a first region and at least a second region, an
 area of the first region being smaller than an area of the second region, and the
 second region being partially overlapped with the first region;
 performing a first etching process upon a first surface of the wafer to remove the
10 wafer in the first region until a predetermined depth;
 bonding the first surface of the wafer to a carrier; and
 performing a second etching process upon a second surface of the wafer to remove a
 portion of the wafer in the second region not overlapped with the first region until
 the wafer is etched through.

15 Claim 2 (original) The method of claim 1, wherein the first region and the second region
 define a micro spindle structure.

20 Claim 3 (previously presented) The method of claim 1, wherein the first etching process
 comprises:
 forming a first photo resist pattern exposing the first region on the first surface of the
 wafer;
 etching the wafer not covered by the first photo resist pattern until the predetermined
 depth, the predetermined depth being larger than a sum of a deviation of the second
25 etching process and a deviation of a thickness of the wafer; and
 removing the first photo resist pattern.

Claim 4 (original) The method of claim 1, wherein the first surface of the wafer is bonded

to the carrier with a bonding layer.

Claim 5 (previously presented) The method of claim 1, wherein the second etching process comprises:

5 forming a second photo resist pattern exposing the second region not overlapped with the first region;
etching through the wafer not covered by the second photo resist pattern until the bonding layer; and
removing the second photo resist pattern.

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Claim 6 (previously presented) The method of claim 1, further comprising performing the step of removing the bonding layer after the second etching process.

Claim 7 (currently amended) A method of forming a micro spindle, comprising:

15 providing a wafer comprising at least a spindle region and two through regions, the two through regions being respectively positioned on both sides of the spindle region;
partially removing the wafer in the spindle region from a first surface of the wafer;
and
20 removing the wafer in the two through regions from a second surface of the wafer until the wafer is removed through to the first surface, wherein the first surface of the wafer is bonded to a carrier with a bonding layer while removing the wafer in the two through regions.

25 Claim 8 (original) The method of claim 7, wherein the wafer in the spindle region is removed by etching.

Claim 9 (original) The method of claim 7, wherein the wafer in the two through regions

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are removed by etching.

Claim 10 (cancelled)

5 Claim 11 (currently amended) The method of claim [[10]] 7, further comprising the step of removing the bonding layer after the wafer in the two through regions is removed.